



1GB – 2x64Mx72 DDR2 SDRAM UNBUFFERED

FEATURES

- 240-pin, dual in-line memory module (DIMM)
- Fast data transfer rates: PC2-6400*, PC2-5300*, PC2-4200 and PC2-3200
- Utilizes 800*, 667*, 533 and 400 MT/s DDR2 SDRAM components
- $V_{CC} = V_{CCQ} = 1.8V \pm 0.1V$
- JEDEC standard 1.8V I/O (SSTL_18-compatible)
- Differential data strobe (DQS, DQS#) option
- Four-bit prefetch architecture
- Programmable CAS# latency (CL): 3, 4, 5 and 6
- On-die termination (ODT)
- Serial Presence Detect (SPD) with EEPROM
- Gold edge contacts
- Dual Rank
- RoHS compliant
- Package
 - 240 Pin DIMM: 30.00mm (1.181") TYP

DESCRIPTION

The WV3HG264M72EEU is a 2x64Mx74 Double Data Rate DDR2 SDRAM high density module. This memory module consists of eighteen 64Mx8 bit with 4 banks DDR2 Synchronous DRAMs in FBGA packages, mounted on a 240-pin DIMM FR4 substrate.

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

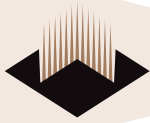
NOTE: Consult factory for availability of:

- Vendor source control options
- Industrial temperature option

OPERATING FREQUENCIES

	PC2-3200	PC2-4200	PC2-5300*	PC2-6400*
Clock Speed	200MHz	266MHz	333MHz	400MHz
CL-t _{RCD} -t _{RP}	3-3-3	4-4-4	5-5-5	6-6-6

* Consult factory for availability



PIN CONFIGURATION

Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol
1	V _{REF}	61	A4	121	V _{SS}	181	V _{CCQ}
2	V _{SS}	62	V _{CCQ}	122	DQ4	182	A3
3	DQ0	63	A2	123	DQ5	183	A1
4	DQ1	64	V _{CC}	124	V _{SS}	184	V _{CC}
5	V _{SS}	65	V _{SS}	125	DM0	185	CK0
6	DQS0#	66	V _{SS}	126	NC	186	CK0#
7	DQS0	67	V _{CC}	127	V _{SS}	187	V _{CC}
8	V _{SS}	68	NC	128	DQ6	188	A0
9	DQ2	69	V _{CC}	129	DQ7	189	V _{CC}
10	DQ3	70	A10/AP	130	V _{SS}	190	BA1
11	V _{SS}	71	BA0	131	DQ12	191	V _{CCQ}
12	DQ8	72	V _{CCQ}	132	DQ13	192	RAS#
13	DQ9	73	WE#	133	V _{SS}	193	CS0#
14	V _{SS}	74	CAS#	134	DM1	194	V _{CCQ}
15	DQS1#	75	V _{CCQ}	135	NC	195	ODT0
16	DQS1	76	CS1#	136	V _{SS}	196	A13
17	V _{SS}	77	ODT1	137	CK1	197	V _{CC}
18	NC	78	V _{CCQ}	138	CK1#	198	V _{SS}
19	NC	79	V _{SS}	139	V _{SS}	199	DQ36
20	V _{SS}	80	DQ32	140	DQ14	200	DQ37
21	DQ10	81	DQ33	141	DQ15	201	V _{SS}
22	DQ11	82	V _{SS}	142	V _{SS}	202	DM4
23	V _{SS}	83	DQS4#	143	DQ20	203	NC
24	DQ16	84	DQS4	144	DQ21	204	V _{SS}
25	DQ17	85	V _{SS}	145	V _{SS}	205	DQ38
26	V _{SS}	86	DQ34	146	DM2	206	DQ39
27	DQS2#	87	DQ35	147	NC	207	V _{SS}
28	DQS2	88	V _{SS}	148	V _{SS}	208	DQ44
29	V _{SS}	89	DQ40	149	DQ22	209	DQ45
30	DQ18	90	DQ41	150	DQ23	210	V _{SS}
31	DQ19	91	V _{SS}	151	V _{SS}	211	DM5
32	V _{SS}	92	DQS5#	152	DQ28	212	NC
33	DQ24	93	DQS5	153	DQ29	213	V _{SS}
34	DQ25	94	V _{SS}	154	V _{SS}	214	DQ46
35	V _{SS}	95	DQ42	155	DM3	215	DQ47
36	DQS3#	96	DQ43	156	NC	216	V _{SS}
37	DQS3	97	V _{SS}	157	V _{SS}	217	DQ52
38	V _{SS}	98	DQ48	158	DQ30	218	DQ53
39	DQ26	99	DQ49	159	DQ31	219	V _{SS}
40	DQ27	100	V _{SS}	160	V _{SS}	220	CK2
41	V _{SS}	101	SA2	161	CB4	221	CK2#
42	CB0	102	NC	162	CB5	222	V _{SS}
43	CB1	103	V _{SS}	163	V _{SS}	223	DM6
44	V _{SS}	104	DQS6#	164	DM8	224	NC
45	DQS8#	105	DQS6	165	NC	225	V _{SS}
46	DQS8	106	V _{SS}	166	V _{SS}	226	DQ54
47	V _{SS}	107	DQ50	167	CB6	227	DQ55
48	CB2	108	DQ51	168	CB7	228	V _{SS}
49	CB3	109	V _{SS}	169	V _{SS}	229	DQ60
50	V _{SS}	110	DQ56	170	V _{CCQ}	230	DQ61
51	V _{CCQ}	111	DQ57	171	CKE1	231	V _{SS}
52	CKE0	112	V _{SS}	172	V _{CC}	232	DM7
53	V _{CC}	113	DQS7#	173	NC	233	NC
54	NC	114	DQS7	174	NC	234	V _{SS}
55	NC	115	V _{SS}	175	V _{CCQ}	235	DQ62
56	V _{CCQ}	116	DQ58	176	A12	236	DQ63
57	A11	117	DQ59	177	A9	237	V _{SS}
58	A7	118	V _{SS}	178	V _{CC}	238	V _{CCSPD}
59	V _{CC}	119	SDA	179	A8	239	SA0
60	A5	120	SCL	180	A6	240	SA1

PIN NAMES

Pin Name	Function
A0-A13	Address Input
BA0, BA1	Bank Address
DQ0 ~ DQ63	Data Input/output
CB0-CB7	Check Bits
DQS0 ~ DQS8	Data Strobe
DQS0# ~ DQS8#	Data Strobe negative
ODT0, ODT1	On Die Termination
CK0, CK0# - CK2, CK2#	Clock Input
CKE0, CKE1	Clock enable input
CS0#, CS1#	Chip Select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
V _{CC}	Voltage Supply (1.8V±0.1V)
V _{CCQ}	I/O Power (1.8V)
V _{SS}	Ground
SA0 ~ SA2	SPD Address
SDA	Serial Data I/O
SCL	Serial clock
DM(0-8)	Data Masks
A10/AP	Address input/Auto precharge
V _{REF}	I/O reference supply
V _{CCSPD}	Serial EEPROM
NC	No Connect



Notes:
1. DQ, DM, DQS, DQS# resistors: 5.1 Ohms +/- 5%
2. BAx, Ax, RAS#, CAS#, WE# resistors: 5.1 Ohms +/- 5%

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DC OPERATING CONDITIONS

All Voltages Referenced to V_{SS}

Parameter	Symbol	Rating			Units	Notes
		Min.	Type	Max.		
Supply Voltage	V _{CC}	1.7	1.8	1.9	V	1
I/O Supply Voltage	V _{CCQ}	1.7	1.8	1.9	V	4
VCCL Supply Voltage	V _{CCL}	1.7	1.8	1.9	V	4
I/O Reference Voltage	V _{REF}	0.49*V _{CCQ}	0.50*V _{CCQ}	0.51*V _{CCQ}	V	2
I/O Termination Voltage	V _{TT}	V _{REF} -0.04	V _{REF}	V _{REF} +0.04	V	3

Notes:

1. V_{CC} and V_{CCQ} must track each other. V_{CCQ} must be less than or equal to V_{CC}.
2. V_{REF} is expected to equal V_{CCQ/2} of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise on V_{REF} may not exceed +/- percent of the DC value. Peak-to-peak AC noise on V_{REF} may not exceed +/-2 percent of V_{REF}. This measurement is to be taken at the nearest V_{REF} bypass capacitor.
3. V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} and must track variations in the DC level of V_{REF}.
4. V_{CCQ} tracks with V_{CC}; V_{CCL} track with V_{CC}.

ABSOLUTE MAXIMUM RATINGS

SSTL_1.8V

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Voltage on V _{CC} pin relative to V _{SS}	- 1.0	2.3	V	
V _{CCQ}	Voltage on V _{CCQ} pin relative to V _{SS}	- 0.5	2.3	V	
V _{CCL}	Voltage on V _{CCL} pin relative to V _{SS}	- 0.5	2.3	V	
V _{IN} , V _{OUT}	Voltage on any pin relative to V _{SS}	- 0.5	2.3	V	
T _{STG}	Storage Temperature	-55	100	°C	
T _{CASE}	Device operating Temperature	0	85	°C	
I _L	Input leakage current; Any input 0V<V _{IN} <V _{CC} ; V _{REF} input 0V<V _{IN} <<0.95; Other pins not under test = 0V	Command/Address, RAS#, CAS#, WE#	-90	90	μA
		CS#, CKE	-45	45	μA
		CK, CK#	-30	30	μA
		DM	-10	10	μA
I _{OZ}	Output leakage current; 0V<V _{OUT} <V _{CCQ} ; DQs and ODT are disable	DQ, DQS, DQS#	-10	10	μA
I _{VREF}	V _{REF} leakage current; V _{REF} = Valid V _{REF} level	-36	36	μA	



CAPACITANCE

$T_A = 25^\circ\text{C}$, $f = 1\text{MHz}$, $V_{CC} = V_{CCQ} = 1.8\text{V}$

Parameter	Symbol	Min	Max	Units
Input Capacitance: (A0 ~ A13, BA0 ~ BA1, RAS#, CAS#, WE#)	C_{IN1}	22	40	pF
Input Capacitance: (CKE0, CKE1), (ODT0, ODT1)	C_{IN2}	13	22	pF
Input Capacitance: (CS0#, CS1#)	C_{IN3}	13	22	pF
Input Capacitance: (CK0, CK0# ~ CK2, CK2#)	C_{IN4}	10	16	pF
Input Capacitance: (DM0 ~ DM8), (DQS0-DQS8)	$C_{IN6} (E6)$	9	11	pF
	$C_{IN6} (D5)$	9	12	pF
Input Capacitance: (DQ0 ~ DQ63), (CB0-CB7)	$C_{OUT1} (E6)$	9	11	pF
	$C_{OUT1} (D5)$	9	12	pF

OPERATING TEMPERATURE CONDITION

Parameter	Symbol	Rating	Units	Notes
Operating Temperature	TOPER	0°C to 85°C	°C	1, 2

Notes:

- Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51.2.
- At 0 - 85°C, operation temperature range, all DRAM specification will be supported.

INPUT DC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Units
Input High (Logic 1) Voltage	$V_{IH(DC)}$	$V_{REF} + 0.125$	$V_{REF} + 0.300$	V
Input Low (Logic 0) Voltage	$V_{IL(DC)}$	-0.300	$V_{REF} - 0.125$	V

INPUT AC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Units
AC Input High (Logic 1) Voltage	$V_{IH(AC)}$	$V_{REF} + 0.250$		V
AC Input Low (Logic 0) Voltage DDR2-400 & DDR2-533	$V_{IL(AC)}$	-	$V_{REF} - 0.250$	V
AC Input Low (Logic 0) Voltage DDR2-667, DDR2-800 (TBD)	$V_{IL(AC)}$	-	$V_{REF} - 0.200$	V



DDR2 I_{CC} SPECIFICATIONS AND CONDITIONS

Symbol	Proposed Conditions	806	665	534	403	Units
I _{CC0} *	Operating one bank active-precharge current; t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RAS} = t _{RAS} min(I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	837	792	792	mA
I _{CC1} *	Operating one bank active-read-precharge current; I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RAS} = t _{RAS} min(I _{CC}), t _{RCD} = t _{RCD} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I _{CC4W}	TBD	972	972	972	mA
I _{CC2P} **	Precharge power-down current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	TBD	144	144	144	mA
I _{CC2Q} **	Precharge quiet standby current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	TBD	630	540	540	mA
I _{CC2N} **	Precharge standby current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	720	630	630	mA
I _{CC3P} **	Active power-down current; All banks open; t _{CK} = t _{CK} (I _{CC}); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	Fast PDN Exit MRS(12) = 0	TBD	540	540	mA
		Slow PDN Exit MRS(12) = 1	TBD	216	216	mA
I _{CC3N} **	Active standby current; All banks open; t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RAS} = t _{RAS} min(I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	990	900	900	mA
I _{CC4W} **	Operating burst write current; All banks open, Continuous burst writes; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RAS} = t _{RAS} max(I _{CC}), t _{TRP} = t _{TRP} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	1332	1152	1062	mA
I _{CC4R} *	Operating burst read current; All banks open, Continuous burst reads, I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RAS} = t _{RAS} max(I _{CC}), t _{TRP} = t _{TRP} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I _{CC4W}	TBD	1377	1197	1062	mA
I _{CC5B} **	Burst auto refresh current; t _{CK} = t _{CK} (I _{CC}); Refresh command at every t _{REFC} (I _{CC}) interval; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	2700	2520	2520	mA
I _{CC6} *	Self refresh current; CK and CK# at 0V; CKE 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	Normal	TBD	144	144	mA
I _{CC7} *	Operating bank interleave read current; All bank interleaving reads, I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = t _{RCD} (I _{CC}) - 1 * t _{CK} (I _{CC}); t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RRD} = t _{RRD} (I _{CC}), t _{RCD} = 1 * t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data bus inputs are switching.	TBD	2052	2052	2052	mA

* Value calculated as one module rank in this operating condition, and all other module ranks in



AC TIMING PARAMETERS

0°C ≤ T_{case} < +85°C; V_{CCQ} = + 1.8V ± 0.1V, V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS				806		665		534		403		
PARAMETER			SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Clock	Clock cycle time	CL = 6	t _{CK} (6)	TBD	TBD							ps
		CL = 5	t _{CK} (5)	TBD	TBD	3000	8000					ps
		CL = 4	t _{CK} (4)	TBD	TBD	3750	8000	3,750	8,000	5,000	8,000	ps
		CL = 3	t _{CK} (3)	TBD	TBD	5000	8000	5,000	8,000	5,000	8,000	ps
	CK high-level width		t _{CH}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t _{CK}
	CK low-level width		t _{CL}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t _{CK}
	Half clock period		t _{HP}	TBD	TBD	MIN (t _{CH} , t _{CL})		MIN (t _{CH} , t _{CL})		MIN (t _{CH} , t _{CL})		ps
Data	DQ output access time from CK/CK#		t _{AC}	TBD	TBD	-450	+450	-500	+500	-600	+600	ps
	Data-out high-impedance window from CK/CK#		t _{HZ}	TBD	TBD		t _{AC} (MAX)		t _{AC} (MAX)		t _{AC} (MAX)	ps
	Data-out low-impedance window from CK/CK#		t _{LZ}	TBD	TBD	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	ps
	DQ and DM input setup time relative to DQS		t _{DS}	TBD	TBD	100		100		150		ps
	DQ and DM input hold time relative to DQS		t _{DH}	TBD	TBD	225		225		275		ps
	A DQ and DM input pulse width (for each input)		t _{DIPW}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	Data hold skew factor		t _{QHS}	TBD	TBD		340		400		450	ps
	DQ...DQS hold, DQS to first DQ to go nonvalid, per access		t _{QH}	TBD	TBD	t _{HP} - t _{QHS}		t _{HP} - t _{QHS}		t _{HP} - t _{QHS}		ps
	Data valid output window (DVW)		t _{DVW}	TBD	TBD	t _{QH} - t _{DQSQ}		t _{QH} - t _{DQSQ}		t _{QH} - t _{DQSQ}		ns
Data Strobe	DQS input high pulse width		t _{DQSH}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS input low pulse width		t _{DQSL}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS output access time from CK/CK#		t _{DQSCK}	TBD	TBD	-400	+400	-450	+450	-500	+500	ps
	DQS falling edge to CK rising ... setup time		t _{DSS}	TBD	TBD	0.2		0.2		0.2		t _{CK}
	DQS falling edge from CK rising ... hold time		t _{DSH}	TBD	TBD	0.2		0.2		0.2		t _{CK}
	DQS...DQ skew, DQS to last DQ valid, per group, per access		t _{DQSQ}	TBD	TBD		240		300		350	ps
	DQS read preamble		t _{RPRE}	TBD	TBD	0.9	1.1	0.9	1.1	0.9	1.1	t _{CK}
	DQS read postamble		t _{RPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
	DQS write preamble setup time		t _{WPRES}	TBD	TBD	0		0		0		ps
	DQS write preamble		t _{WPRE}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS write postamble		t _{WPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
	Write command to first DQS latching transition		t _{DQSS}	TBD	TBD	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	t _{CK}
	Address and control input pulse width for each input		t _{IPW}	TBD	TBD	0.6		0.6		0.6		t _{CK}

NOTE:

- AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

Continued on next page



AC TIMING PARAMETERS (cont'd)

0°C ≤ T_{case} < +85°C; V_{CCQ} = +1.8V ± 0.1V, V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS			806		665		534		403		
PARAMETER		SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Command and Address	Address and control input setup time	t _{IS}	TBD	TBD	200		250		250		ps
	Address and control input hold time	t _{IH}	TBD	TBD	275		375		475		ps
	CAS# to CAS# command delay	t _{CCD}	TBD	TBD	2		2		2		tck
	ACTIVE to ACTIVE (same bank) command	t _{RC}	TBD	TBD	55		55		55		ns
	ACTIVE bank a to ACTIVE bank b command	t _{RRD}	TBD	TBD	7.5		7.5		7.5		ns
	ACTIVE to READ or WRITE delay	t _{RCD}	TBD	TBD	15		15		15		ns
	Four Bank Activate period	t _{FAW}	TBD	TBD	37.5	37.5	37.5	37.5	37.5	37.5	
	ACTIVE to PRECHARGE command	t _{RAS}	TBD	TBD	45	70,000	45	70,000	45	70,000	ns
	Internal READ to precharge command delay	t _{RTP}	TBD	TBD	7.5		7.5		7.5		ns
	Write recovery time	t _{WR}	TBD	TBD	15		15		15		ns
	Auto precharge write recovery + precharge time	t _{DAL}	TBD	TBD	t _{WR} + t _{RP}		t _{WR} + t _{RP}		t _{WR} + t _{RP}		ns
	Internal WRITE to READ command delay	t _{WTR}	TBD	TBD	10		7.5		10		ns
	PRECHARGE command period	t _{RP}	TBD	TBD	15		15		15		
	PRECHARGE ALL command period	t _{RPA}	TBD	TBD	t _{WR} + t _{CK}		t _{WR} + t _{CK}		t _{WR} + t _{CK}		ns
	LOAD MODE command cycle time	t _{MRD}	TBD	TBD	2		2		2		tck
Refresh	CKE low to CK,CK# uncertainty	t _{DELAY}	TBD	TBD	t _{IS} + t _{CK} + t _{IH}		t _{IS} + t _{CK} + t _{IH}		t _{IS} + t _{CK} + t _{IH}		ns
	REFRESH to REFRESH command interval	t _{RFC}	TBD	TBD	127.5	70,000	127.5	70,000	127.5	70,000	ns
Self Refresh	Average periodic refresh interval	t _{REFI}	TBD	TBD		7.8		7.8		7.8	μs
	Exit self refresh to non-READ command	t _{XSNR}	TBD	TBD	t _{RFC} (MIN) + 10		t _{RFC} (MIN) + 10		t _{RFC} (MIN) + 10		ns
ODT	Exit self refresh to READ command	t _{XSRD}	TBD	TBD	200		200		200		tck
	Exit self refresh timing reference	t _{ISXR}	TBD	TBD	t _{IS}		t _{IS}		t _{IS}		ps
	ODT turn-on delay	t _{AOND}	TBD	TBD	2	2	2	2	2	2	tck
	ODT turn-on	t _{AON}	TBD	TBD	t _{AC} (MIN)	t _{AC} (MAX) + 1000	t _{AC} (MIN)	t _{AC} (MAX) + 1000	t _{AC} (MIN)	t _{AC} (MAX) + 1000	ps
	ODT turn-off delay	t _{AOFD}	TBD	TBD	2.5	2.5	2.5	2.5	2.5	2.5	tck
	ODT turn-off	t _{AOF}	TBD	TBD	t _{AC} (MIN)	t _{AC} (MAX) + 600	t _{AC} (MIN)	t _{AC} (MAX) + 600	t _{AC} (MIN)	t _{AC} (MAX) + 600	ps
	ODT turn-on (power-down mode)	t _{AONPD}	TBD	TBD	t _{AC} (MIN) + 2000	2 x t _{CK} + t _{AC} (MAX) + 1000	t _{AC} (MIN) + 2000	2 x t _{CK} + t _{AC} (MAX) + 1000	t _{AC} (MIN) + 2000	2 x t _{CK} + t _{AC} (MAX) + 1000	ps
	ODT turn-off (power-down mode)	t _{AOFPD}	TBD	TBD	t _{AC} (MIN) + 2000	2.5 x t _{CK} + t _{AC} (MAX) + 1000	t _{AC} (MIN) + 2000	2.5 x t _{CK} + t _{AC} (MAX) + 1000	t _{AC} (MIN) + 2000	2.5 x t _{CK} + t _{AC} (MAX) + 1000	ps
	ODT to power-down entry latency	t _{ANPD}	TBD	TBD	3		3		3		tck
	ODT power-down exit latency	t _{AXPD}	TBD	TBD	8		8		8		tck
Power-Down	Exit active power-down to READ command, MR[bit12=0]	t _{XARD}	TBD	TBD	2		2		2		tck
	Exit active power-down to READ command, MR[bit12=1]	t _{XARDS}	TBD	TBD	7-AL		6-AL		6-AL		tck
	A Exit precharge power-down to any non-READ command.	t _{XP}	TBD	TBD	2		2		2		tck
	CKE minimum high/low time	t _{CKE}	TBD	TBD	3		3		3		tck

NOTE:

- AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.



ORDERING INFORMATION FOR D6

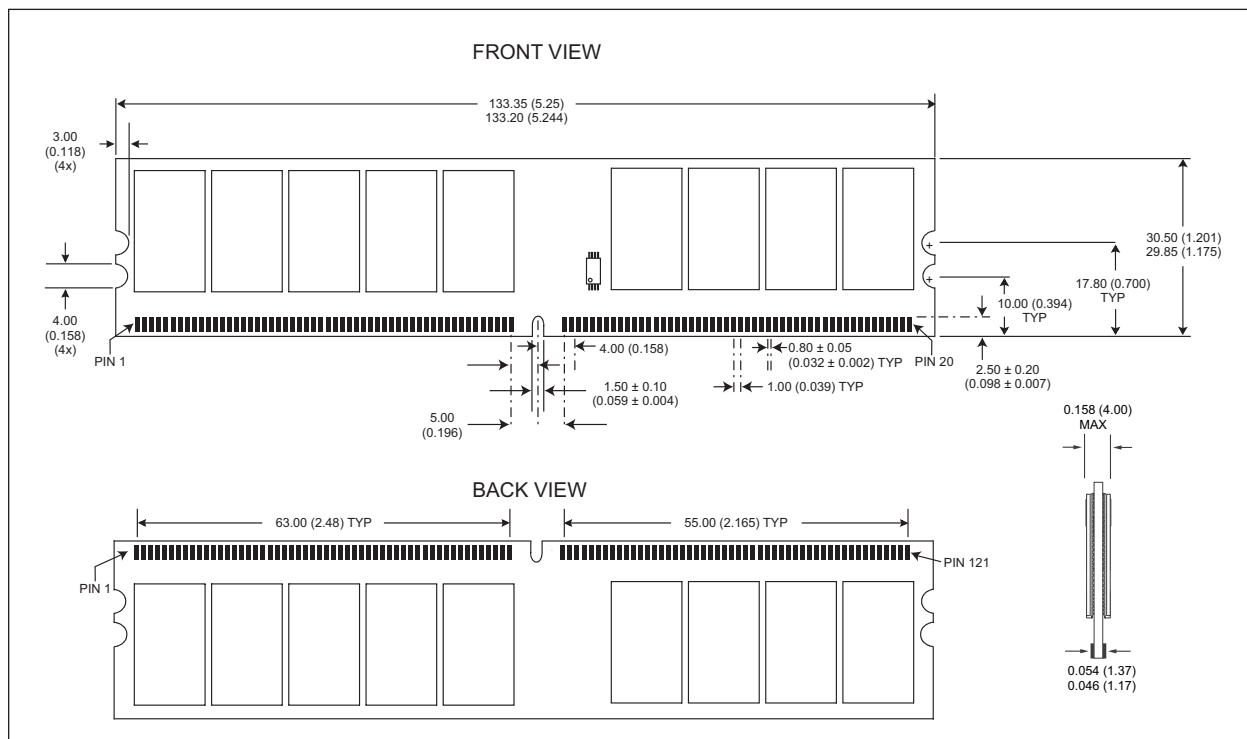
Part Number	Clock/Data Rate Frequency	CAS Latency	t _{RCD}	t _{RP}	Height*
W3HG264M72EEU806D6xG**	400MHz/800Mb/s	6	6	6	30.00mm (1.181") TYP
W3HG264M72EEU665D6xG**	333MHz/667Mb/s	5	5	5	30.00mm (1.181") TYP
W3HG264M72EEU534D6xG	266MHz/533Mb/s	4	4	4	30.00mm (1.181") TYP
W3HG264M72EEU403D6xG	200MHz/400Mb/s	3	3	3	30.00mm (1.181") TYP

** Consult factory for availability

NOTES:

- RoHS compliant product. (G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory component source control. The place holder for this is shown as a lower case "x" in the part numbers above and is to be replaced with respective vendors code. Consult factory for qualified sourcing options.
(G = Infineon, M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

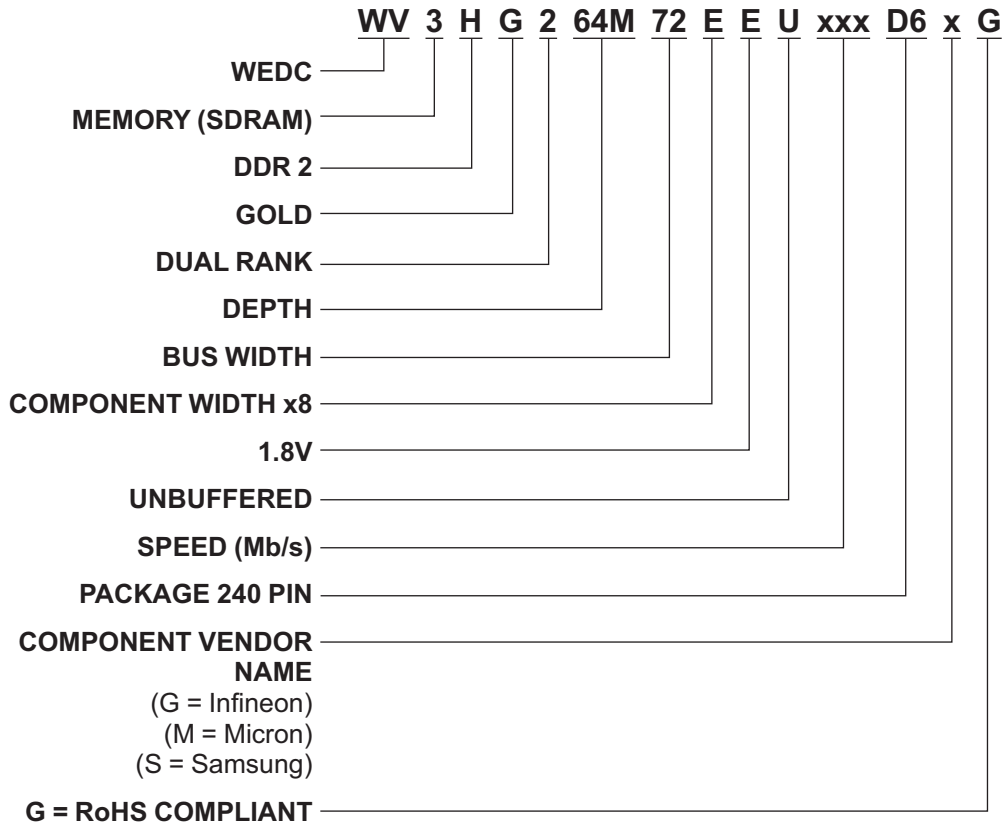
PACKAGE DIMENSIONS FOR D6



* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)



PART NUMBERING GUIDE





Document Title

1GB – 2x64Mx72 DDR2 SDRAM UNBUFFERED

Revision History

Rev #	History	Release Date	Status
Rev 0	Created	January 2006	Advanced